MJ15023 (PNP), **MJ15025 (PNP)**

Silicon Power Transistors

The MJ15023 and MJ15025 are power transistors designed for high power audio, disk head positioners and other linear applications.

Features

- High Safe Operating Area (100% Tested) -2 A @ 80 V
- High DC Current Gain $h_{FE} = 15$ (Min) @ $I_C = 8$ Adc
- Pb-Free Packages are Available*

MAXIMUM RATINGS

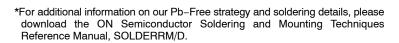
Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJ15023 MJ15025	V _{CEO}	200 250	Vdc
Collector-Base Voltage MJ15023 MJ15025	V _{CBO}	350 400	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector-Emitter Voltage	V _{CEX}	400	Vdc
Collector Current - Continuous - Peak (Note 1)	I _C	16 30	Adc
Base Current - Continuous	I _B	5	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.



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16 AMPERES SILICON POWER TRANSISTORS 200 - 250 VOLTS, 250 WATTS



TO-204AA (TO-3) **CASE 1-07** STYLE 1

MARKING DIAGRAM



MJ1502x = Device Code

x = 3 or 5

G = Pb-Free Package = Assembly Location

= Year WW = Work Week = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
MJ15023	TO-204	100 Units / Tray
MJ15023G	TO-204 (Pb-Free)	100 Units / Tray
MJ15025	TO-204	100 Units / Tray
MJ15025G	TO-204 (Pb-Free)	100 Units / Tray

MJ15023 (PNP), MJ15025 (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 100 \text{ mAdc}, I_B = 0)$	MJ15023 MJ15025	V _{CEO(sus)}	200 250	- -	-
Collector Cutoff Current (V _{CE} = 200 Vdc, V _{BE(off)} = 1.5 Vdc) (V _{CE} = 250 Vdc, V _{BE(off)} = 1.5 Vdc)	MJ15023 MJ15025	I _{CEX}	- -	250 250	μAdc
Collector Cutoff Current $(V_{CE} = 150 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 200 \text{ Vdc}, I_B = 0)$	MJ15023 MJ15025	I _{CEO}	- -	500 500	μAdc
Emitter Cutoff Current $(V_{CE} = 5 \text{ Vdc}, I_B = 0)$	Both	I _{EBO}	-	500	μAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 50 \text{ Vdc}$, $t = 0.5 \text{ s (non-repetitive)}$) ($V_{CE} = 80 \text{ Vdc}$, $t = 0.5 \text{ s (non-repetitive)}$)		I _{S/b}	5 2	- -	Adc
ON CHARACTERISTICS		•			
DC Current Gain ($I_C = 8$ Adc, $V_{CE} = 4$ Vdc) ($I_C = 16$ Adc, $V_{CE} = 4$ Vdc)		h _{FE}	15 5	60 -	-
Collector–Emitter Saturation Voltage ($I_C = 8$ Adc, $I_B = 0.8$ Adc) ($I_C = 16$ Adc, $I_B = 3.2$ Adc)		V _{CE(sat)}	- -	1.4 4.0	Vdc
Base–Emitter On Voltage ($I_C = 8$ Adc, $V_{CE} = 4$ Vdc)		V _{BE(on)}	-	2.2	Vdc
DYNAMIC CHARACTERISTICS			,		•
Current-Gain - Bandwidth Product ($I_C = 1$ Adc, $V_{CE} = 10$ Vdc, $f_{test} = 1$ MHz)		f _T	4	-	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f_{test} = 1 \text{ MHz}$)		C _{ob}	-	600	pF

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

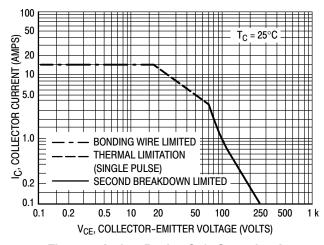


Figure 1. Active-Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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TYPICAL CHARACTERISTICS

1.8

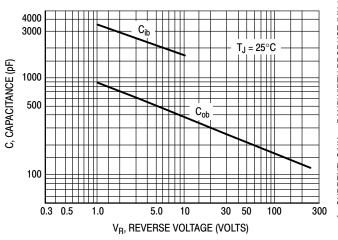
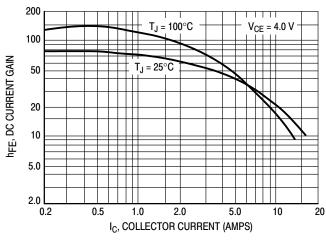


Figure 2. Capacitances

Figure 3. Current-Gain — Bandwidth Product



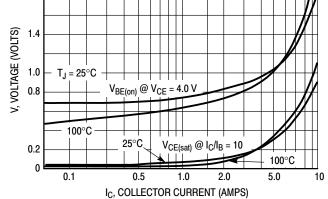


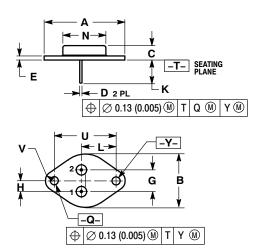
Figure 4. DC Current Gain

Figure 5. "On" Voltages

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PACKAGE DIMENSIONS

TO-204 (TO-3) **CASE 1-07** ISSUE Z



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION: INCH.
- 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37	REF	
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Ε	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187	BSC	30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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